

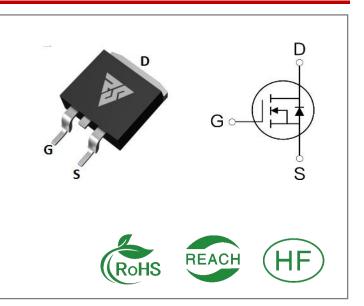
ID	R _{Ds} (ON)(Typ)	VDSS
20A	0.21Ω	500V

Applications:

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability



Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS20N50S	T0-263	RS20N50S	Tape&reel	800 PCS

Absolute Maximun Ratings Tc= 25°C unless otherwise specified

Symbol	Parameter	RS20N50S	Units
VDSS	Drain-to-Source Voltage	500	V
ID	Continuous Drain Current TC=25℃	20	٨
IDM	Pulsed Drain Current (Note*1)	80	A
PD	Power Dissipation	173	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH,,VDD = 50V, RG = 25Ω	650	mJ
	Maximum Temperature for Soldering		
TL TPKG	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	300 260	Ĉ
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.



Thermal Resistance

Symbol	Parameter	RS20N50S	Units	Test Conditions
RθJC	Junction-to-Case	0.72	°C/W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 $^\circ\!\!C$
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25° C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	500			V	VGS=0V,ID=250μ Α
IDSS	Drain- to- Source Leakage Current			1	μΑ	VDS=500V,VGS= 0V
	Gate- to- Source Forward Leakage			100	~ ^	VGS=30V ,VDS=0 V
IGSS	Gate- to- Source Reverse Leakage			-100	nA	VGS=-30V ,VDS= 0V

ON Characteristics TJ=25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On- Resistance(Note*2)		0.21	0.27	Ω	VGS=10V,ID=10A
VGS(TH)	Gate Threshold Voltage	3		4	V	VGS=VDS,ID=25 0μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time		55			
trise	Rise Time		32			VDS=250V
td(OFF)	Turn- OFF Delay Time		226		nS	ID=20A RG=25Ω
tfall	Fall Time		58			



Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
Ciss	Input Capacitance		2707			VGS=0V
Coss	Output Capacitance		292		pF	VDS=25V
Crss	Reverse Transfer Capacitance		10.5			f=1.0MHz
Qg	Total Gate Charge		49			VDS=400V
Qgs	Gate- to- Source Charge		13.3		nC	ID=20A
Qgd	Gate-to-Drain(" Miller") Charge		17.9			VGS=10V

Dynamic Characteristics Essentially independent of operating temperature

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
IS	Continuous Source Current			20	А	Integral pn- diode
ISM	Maximum Pulsed Current			80	А	in MOSFET
VSD	Diode Forward Voltage			1.2	V	IS=10A,VGS=0V
trr	Reverse Recovery Time		318		nS	VGS=0V
Qrr	Reverse Recovery Charge		4.5		μC	IS=20A,di/dt=100 A/µs

Notes:

- * 1. Repetitive rating, pulse width limited by maximum junction temperature.
- * 2. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



Typical Feature Curve



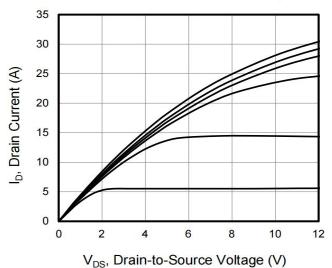


Figure 3. Drain Current vs. Temperature

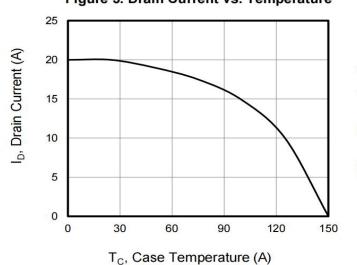


Figure 5. Transfer Characteristics 25 R_{DS(on)}, On-Resistance (Normalized) T_J = 25°C 20 I_D, Drain Current (A) 15 T_J = 150°C 10 5 0 0 2 4 6 8 10 V_{GS}, Gate-to-Source Voltage (V)

Figure 2. Body Diode Forward Voltage

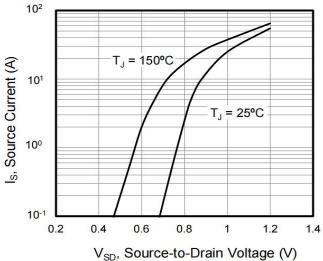


Figure 4. BV_{DSS} Variation vs. Temperature

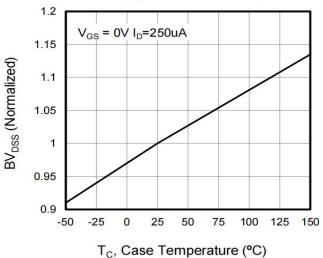
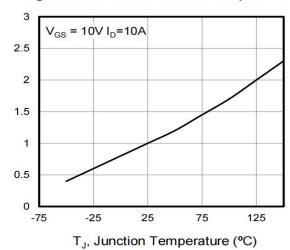
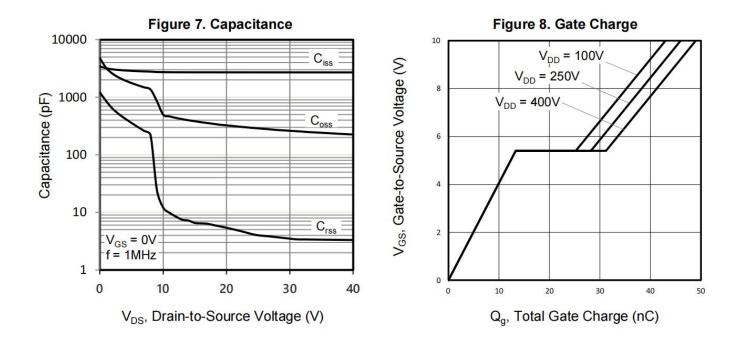


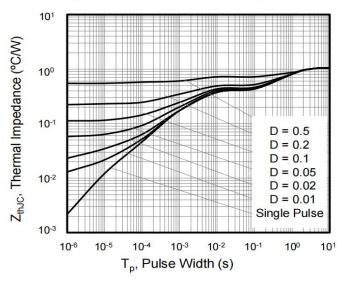
Figure 6. On-Resistance vs. Temperature













Test Circuits and Waveforms



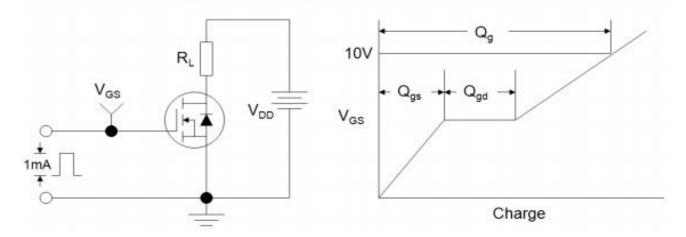


Figure B: Resistive Switching Test Circuit and Waveform

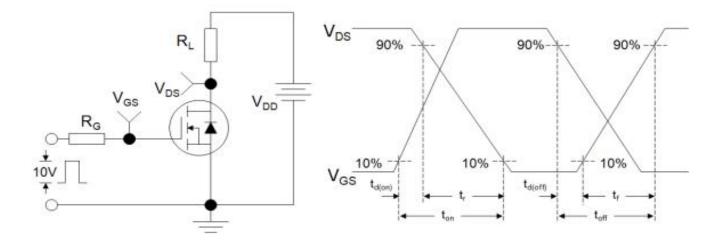
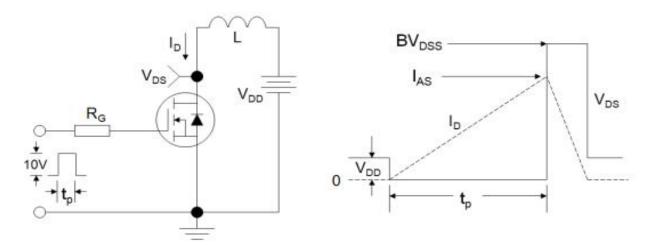
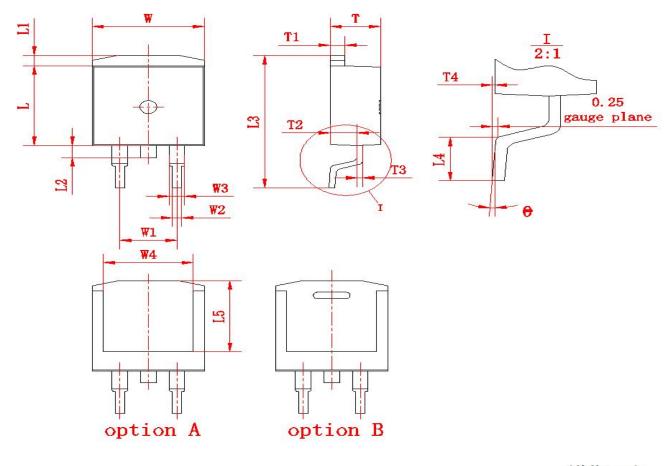


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





Package outline drawing(TO-263 Unit: mm)



(单位: mm)

か つ	尺寸		竹口	尺寸		75 日	尺寸	
符号	Min	Max	符号	Min	Max	符号	Min	Max
W	9.80	10.20	L1	1.00	1.40	T1	1.20	1.40
W 1	(5.	08)	L2	1.20	1.60	T2	2.20	2.60
W2	0.70	0.95	L3	15.00	15. 60	Т3	0.45	0.65
W3	1.17	1.62	L4	2.20	2.80	T4	0	0.25
W 4	(8)	. 0)	L5	(8. 2)		θ	0°	8°
L	9.00	9.40	Т	4. 30	4.70			-



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